

(use as many sheets as necessary)

Sheet	A1	of	A1
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Application Number	10/560,488
Filing Date	December 12, 2005
First Named Inventor	Gerald Lucovsky
Confirmation No.	3119
Examiner Name	Benjamin P. Sandvik
Attorney Docket Number	5051-639

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OTHER NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published		T
	2.	Woo Sik Kim; Ferroelectric-gate field effect transistors using Nd₂TiO₇/Y₂O₃/Si structures; Thin Solid Films 398-399 (2001) 663-667.		
	3.	Seung-Gu Lim; Dielectric functions and optical bandgaps of high-K dielectrics for metal-oxide-semiconductor field-effect transistors by far ultraviolet spectroscopic ellipsometry; Journal of Applied Physics, Volume: 91, Number 7, pp 4500-4505 (April 1, 2002).		
	4.	J.K. Yamamoto; Microwave dielectric properties of layered perovskite A₂B₂O₇ single-crystal fibers; Elsevier Science Publishers B.V. (North-Holland (1991) Material Letters No. 11/12 pp 497-500.		
	5.	European communication with European Search Report for Application No. 04776548.2 – 1235 PCT/US2004018863, dated 5-6-2008.		

/Benjamin Sandvik/ (09/03/2008)

Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and examiner considered. Include copy of string to the written part of the communication to the applicant.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /B.S./